Atomic layer-deposited (HfZrO4)1−x(SiO2)x thin films for gate stack applications

Pyungho Choi, Dohyun Baek, Sung Heo, Byoungdeog Choi

PII:	S0040-6090(17)30925-2
DOI:	https://doi.org/10.1016/j.tsf.2017.12.020
Reference:	TSF 36394
To appear in:	*Thin Solid Films*
Received date:	6 June 2017
Revised date:	18 December 2017
Accepted date:	20 December 2017

Please cite this article as: Pyungho Choi, Dohyun Baek, Sung Heo, Byoungdeog Choi , Atomic layer-deposited (HfZrO4)1−x(SiO2)x thin films for gate stack applications. The address for the corresponding author was captured as affiliation for all authors. Please check if appropriate. Tsf(2017), https://doi.org/10.1016/j.tsf.2017.12.020

Atomic Layer-Deposited $(HfZrO_4)_{1-x}(SiO_2)_x$ Thin Films for Gate Stack Applications

Pyungho Choi[a], Dohyun Baek[a], Sung Heo[b], and Byoungdeog Choi[a,]*

[a]College of Information and Communication Engineering, Sungkyunkwan University, 2066 Seobu-ro, Jangan-gu, Suwon-si, Gyeonggi-do 16419, Republic of Korea

[b]Analytical Engineering Group, Samsung Advanced Institute of Technology, 130, Samsung-ro, Yeongtong-gu, Suwon-si, Gyeonggi-do 16678, Republic of Korea